

# Single Micropower, Chopper Stabilized, RRIO Operational Amplifier

#### ISL28133

The ISL28133 is a single micropower, chopper stabilized operational amplifier that is optimized for single supply operation from 1.65V to 5.5V. Its low supply current of  $18\mu A$  and wide input range enable the ISL28133 to be an excellent general purpose op amp for a range of applications. The ISL28133 is ideal for handheld devices that operates off 2 AA or single Li-ion batteries.

The ISL28133 is available in the 5 Ld SOT-23, the 5 Ld SC70 and the 6 Ld 1.6mmx1.6mm  $\mu$ TDFN packages. All devices operates over the extended temperature range of -40 °C to +125 °C.

#### **Related Literature**

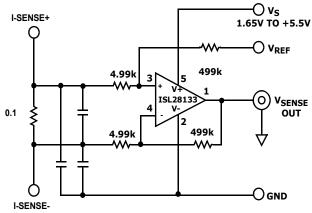
- AN1480 "ISL28133ISENS-EV1Z Evaluation Board Users Guide"
- AN1499 "ISL28133EVAL1Z High Gain Evaluation Board User's Guide"

#### **Features**

Low Input Offset Voltage	8µV, Max.
Low Offset TC	. 0.075μV/°C, Max
Input Bias Current	300pA, Max.
Quiescent Current	
Wide Supply Range	1.65V to 5.5V
• Low Noise (0.01Hz to 10Hz)	1.1μV <sub>P-P</sub> , Typ.
Rail-to-Rail Inputs and Output	
Operating Temperature Range	40°C to +125°C

### **Applications**

- Bidirectional Current Sense
- Temperature Measurement
- Medical Equipment
- Electronic Weigh Scales



BIDIRECTIONAL CURRENT SENSE AMPLIFIER FIGURE 1. TYPICAL APPLICATION CIRCUIT

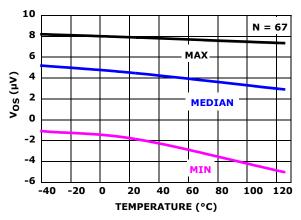
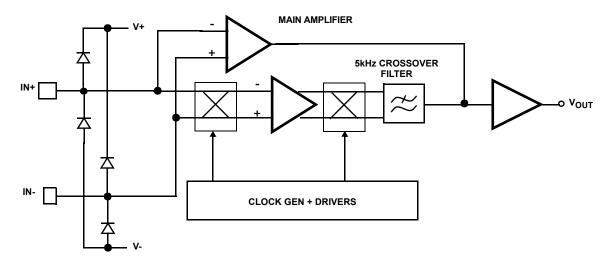


FIGURE 2. VOS vs TEMPERATURE

## **Block Diagram**



## **Ordering Information**

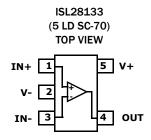
PART NUMBER	PART MARKING	PACKAGE Tape & Reel (Pb-Free)	PKG. DWG. #
ISL28133FHZ-T7 (Notes 1, 2)	BCFA	5 Ld SOT-23	P5.064A
ISL28133FHZ-T7A (Notes 1, 2)	BCFA	5 Ld SOT-23	P5.064A
ISL28133FEZ-T7 (Notes 1, 2)	ВНА	5 Ld SC70	P5.049
ISL28133FRUZ-T7 (Notes 1, 3)	Т8	6 Ld μTDFN	L6.1.6x1.6
ISL28133ISENS-EV1Z	Evaluation Board		
ISL28133EVAL1Z	Evaluation Board		

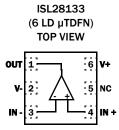
#### NOTES:

- 1. Please refer to TB347 for details on reel specifications.
- These Intersil Pb-free plastic packaged products employ special Pb-free material sets, molding compounds/die attach materials, and 100% matte tin plate
  plus anneal (e3 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations). Intersil Pb-free products are
  MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.
- 3. These Intersil Pb-free plastic packaged products employ special Pb-free material sets; molding compounds/die attach materials and NiPdAu plate e4 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.
- 4. For Moisture Sensitivity Level (MSL), please see device information page for ISL28133. For more information on MSL please see techbrief TB363.

## **Pin Configuration**

ISL28133 (5 LD SOT-23) TOP VIEW OUT 1 5 V+ V- 2 4 IN-





## **Pin Descriptions**

ISL28133 (5 Ld S0T23)	ISL28133 (5 Ld SC70)	ISL28133 (6 Ld µTDFN)	PIN NAME	FUNCTION	EQUIVALENT CIRCUIT
3	1	4	IN+	Non-inverting input	IN- CLOCK GEN + DRIVERS  Circuit 1
2	2	2	V-	Negative supply	OHOUR I
4	3	3	IN-	Inverting input	(See Circuit 1)
1	4	1	оит	Output	V+ OUT V- Circuit 2
5	5	6	V+	Positive supply	
		5	NC	Not Connected - Th	nis pin is not electrically connected internally.

#### **Absolute Maximum Ratings**

Max Supply Voltage V+ to V	6.5V
Max Voltage VIN to GND	-0.5V to 6.5V
Max Input Differential Voltage	6.5V
Max Input Current	20mA
Max Voltage VOUT to GND (10s)	6.5V
ESD Rating	
Human Body Model	3000V
Machine Model	200V
Charged Device Model	1500V

#### **Thermal Information**

Thermal Resistance (Typical, Note 5)	$\theta_{JA}(^{\circ}C/W)$
5 Ld SOT-23	225
5 Ld SC70	206
6 Ld μTDFN	240
Maximum Storage Temperature Range	65°C to +150°C
Pb-Free Reflow Profile	see link below
http://www.intersil.com/pbfree/Pb-FreeReflow.asp	

### **Operating Conditions**

Temperature Range	40°C to	+125°C
Maximum Junction Temperature		.140°C

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

#### NOTE:

5. θ<sub>JA</sub> is measured with the component mounted on a high effective thermal conductivity test board in free air. See Tech Brief TB379 for details.

**Electrical Specifications**  $V_{+} = 5V$ ,  $V_{-} = 0V$ , VCM = 2.5V,  $T_{A} = +25$ °C,  $R_{L} = 0$ pen, unless otherwise specified. **Boldface limits** apply over the operating temperature range, -40°C to +125°C.

PARAMETER	DESCRIPTION	CONDITIONS	MIN (Note 6)	TYP	MAX (Note 6)	UNIT
DC SPECIFICATIONS			•	"		
V <sub>OS</sub>	Input Offset Voltage		-8	±2	8	μV
			-15.5		15.5	μV
TCV <sub>OS</sub>	Input Offset Voltage Temperature Coefficient			0.02	0.075	μV/°C
I <sub>os</sub>	Input Offset Current			-60		pА
I <sub>B</sub>	Input Bias Current		-300	±30	300	pА
			-600		600	pА
Common Mode Input Voltage Range		V+ = 5.0V, V- = GND	-0.1		5.1	V
CMRR	Common Mode Rejection Ratio	VCM = -0.1V to 5.0V	118	125		dB
			115			dB
PSRR	Power Supply Rejection Ratio	Vs = 2V to 5.5V	110	138		dB
			110			dB
V <sub>OH</sub>	Output Voltage Swing, High	$R_L = 10k\Omega$	4.965	4.981		V
V <sub>OL</sub>	Output Voltage Swing, Low	$R_L = 10k\Omega$		18	35	mV
A <sub>OL</sub>	Open Loop Gain	$R_L = 1M\Omega$		174		dB
V <sub>+</sub>	Supply Voltage	(Note 7)	1.65		5.5	V
Is	Supply Current	R <sub>L</sub> = OPEN		18	25	μΑ
					35	μΑ
I <sub>SC+</sub>	Output Source Short Circuit Current	R <sub>L</sub> = Short to ground or V+	13	17	26	mA
I <sub>SC-</sub>	Output Sink Short Circuit Current		-26	-19	-13	mA
AC SPECIFICATIONS	•	<u>,                                      </u>	•			
GBWP	Gain Bandwidth Product f = 50kHz	$\begin{aligned} & \textbf{A}_{\text{V}} = \textbf{100},  \textbf{R}_{\text{F}} = \textbf{100} \textbf{k} \boldsymbol{\Omega}, \\ & \textbf{R}_{\text{G}} = \textbf{1} \textbf{k} \boldsymbol{\Omega},  \textbf{R}_{\text{L}} = \textbf{10} \textbf{k} \boldsymbol{\Omega}  \textbf{to}  \textbf{V}_{\text{CM}} \end{aligned}$		400		kHz
e <sub>N</sub> V <sub>P-P</sub>	Peak-to-Peak Input Noise Voltage	f = 0.01Hz to 10Hz		1.1		μV <sub>P-P</sub>

**Electrical Specifications**  $V_{+} = 5V$ ,  $V_{-} = 0V$ , VCM = 2.5V,  $T_{A} = +25$ °C,  $R_{L} = 0$ pen, unless otherwise specified. **Boldface limits** apply over the operating temperature range, -40°C to +125°C. (Continued)

PARAMETER	DESCRIPTION	conditions	MIN (Note 6)	ТҮР	MAX (Note 6)	UNIT
e <sub>N</sub>	Input Noise Voltage Density	f = 1kHz		65		nV/√(Hz)
i <sub>N</sub>	Input Noise Current Density	f = 1kHz		72		fA/√(Hz)
		f = 10Hz		79		$fA/\sqrt{(Hz)}$
C <sub>in</sub>	Differential Input Capacitance	f = 1MHz		1.6		pF
	Common Mode Input Capacitance	ce		1.12		pF
TRANSIENT RESPON	SE				1	1
SR	Positive Slew Rate	$V_{OUT}$ = 1V to 4V, $R_L$ = 10k $\Omega$		0.2		V/µs
	Negative Slew Rate			0.1		V/µs
t <sub>r</sub> , t <sub>f</sub> , Small Signal	Rise Time, t <sub>r</sub> 10% to 90%	$A_V = +1, V_{OUT} = 0.1V_{P-P},$		1.1		μs
	Fall Time, t <sub>f</sub> 10% to 90%	$R_F = 0\Omega$ , $R_L = 10k\Omega$ , $C_L = 1.2pF$		1.1		μs
t <sub>r</sub> , t <sub>f</sub> Large Signal	Rise Time, t <sub>r</sub> 10% to 90%	$A_V = +1$ , $V_{OUT} = 2V_{P-P}$ , $R_F = 0\Omega$ ,		8		μs
	Fall Time, t <sub>f</sub> 10% to 90%	$R_L = 10k\Omega, C_L = 1.2pF$		10		μs
t <sub>s</sub>	Settling Time to 0.1%, 2V <sub>P-P</sub> Step	$\begin{aligned} \mathbf{A_V} &= +1,  \mathbf{R_F} = 0\Omega,  \mathbf{R_L} = 10 \mathbf{k}\Omega, \\ \mathbf{C_L} &= \mathbf{1.2pF} \end{aligned}$		35		μs

#### NOTES:

- 6. Compliance to datasheet limits is assured by one or more methods: production test, characterization and/or design.
- 7. Parts are 100% tested with a minimum operating voltage of 1.65V to a VOS limit of  $\pm 15 \mu V$ .

## **Typical Performance Curves** $v_{+} = 5V$ , $v_{-} = 0V$ , $V_{CM} = 2.5V$ , $R_{L} = o_{pen}$ .

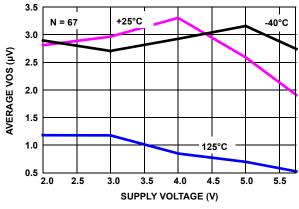


FIGURE 3. AVERAGE INPUT OFFSET VOLTAGE vs SUPPLY VOLTAGE

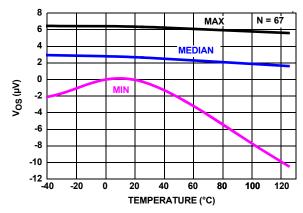
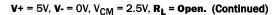


FIGURE 4.  $V_{OS}$  vs TEMPERATURE,  $V_{S}$  = ±1.0V,  $V_{IN}$  = 0V,  $R_{I}$  = INF

## **Typical Performance Curves** v+=5V, v-=0V, $V_{CM}=2.5V$ , $R_L=0$ pen. (Continued)



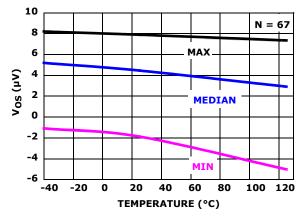


FIGURE 5.  $V_{OS}$  vs TEMPERATURE,  $V_S = \pm 2.5V$ ,  $V_{IN} = 0V$ ,  $R_L =$ 

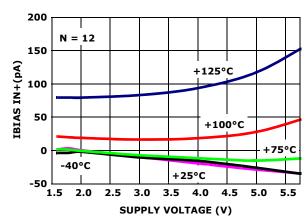


FIGURE 6. IB+ vs SUPPLY VOLTAGE vs TEMPERATURE

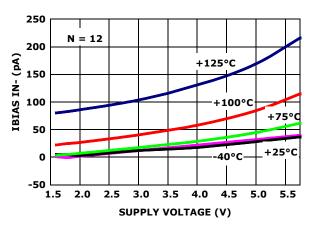


FIGURE 7. IB- vs SUPPLY VOLTAGE vs TEMPERATURE

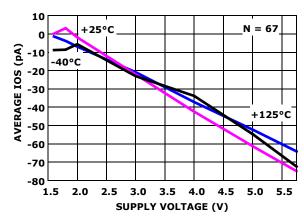


FIGURE 8. IOS vs SUPPLY VOLTAGE vs TEMPERATURE

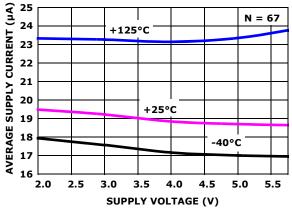


FIGURE 9. AVERAGE SUPPLY CURRENT vs SUPPLY VOLTAGE

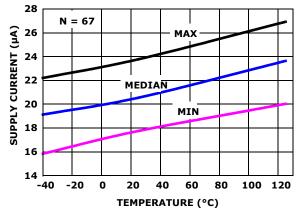


FIGURE 10. MIN/MAX SUPPLY CURRENT vs TEMPERATURE,  $V_S = \pm 0.8V$ ,  $V_{IN} = 0V$ ,  $R_L = INF$ 

## **Typical Performance Curves**



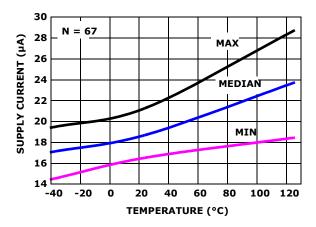


FIGURE 11. MIN/MAX SUPPLY CURRENT vs TEMPERATURE,  $V_S=\pm 2.5 V,\, V_{IN}=0 V,\, R_L=INF$ 

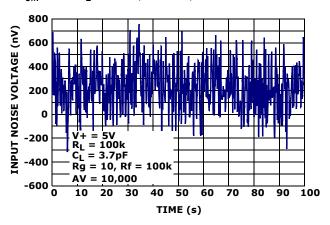


FIGURE 12. INPUT NOISE VOLTAGE 0.01Hz TO 10Hz

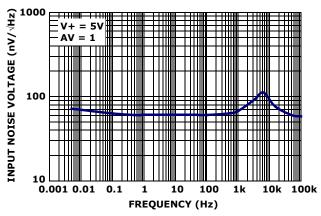


FIGURE 13. INPUT NOISE VOLTAGE DENSITY vs FREQUENCY

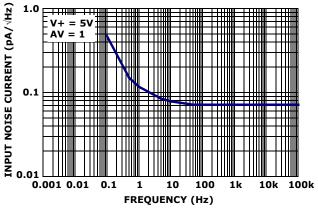


FIGURE 14. INPUT NOISE CURRENT DENSITY vs FREQUENCY

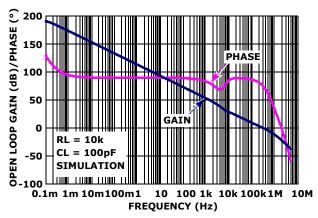


FIGURE 15. FREQUENCY RESPONSE vs OPEN LOOP GAIN, R<sub>L</sub> = 10k

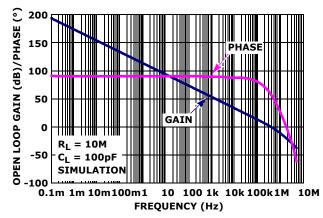
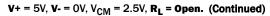


FIGURE 16. FREQUENCY RESPONSE vs OPEN LOOP GAIN, R<sub>L</sub> = 10M

## **Typical Performance Curves**



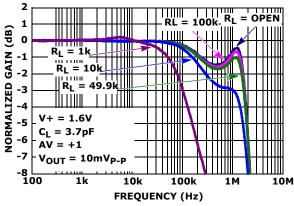


FIGURE 17. GAIN vs FREQUENCY vs  $R_{L}$ ,  $V_S = 1.6V$ 

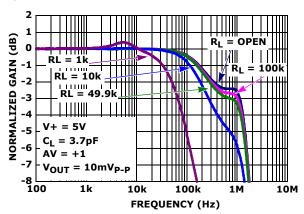


FIGURE 18. GAIN vs FREQUENCY vs R<sub>L</sub>, V<sub>S</sub> = 5V

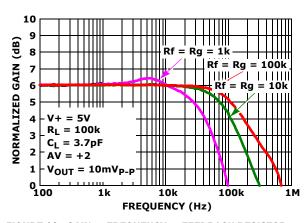


FIGURE 19. GAIN vs FREQUENCY vs FEEDBACK RESISTOR VALUES  $R_f/R_g$ 

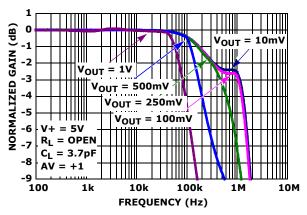


FIGURE 20. GAIN vs FREQUENCY vs V<sub>OUT.</sub> R<sub>L</sub> = OPEN

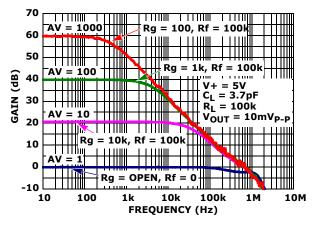


FIGURE 21. FREQUENCY RESPONSE vs CLOSED LOOP GAIN

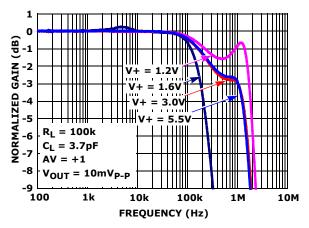
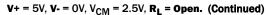


FIGURE 22. GAIN vs FREQUENCY vs SUPPLY VOLTAGE

## Typical Performance Curves $v_+ = 5V$ , $v_- = 0V$ , $V_{CM} = 2.5V$ , $R_L = 0$ pen. (Continued)



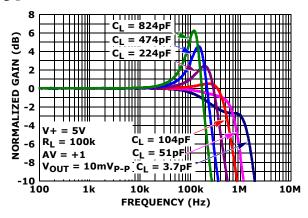


FIGURE 23. GAIN vs FREQUENCY vs CL

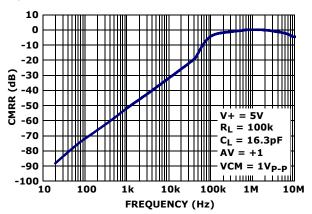


FIGURE 24. CMRR vs FREQUENCY, V<sub>S</sub> = 5V

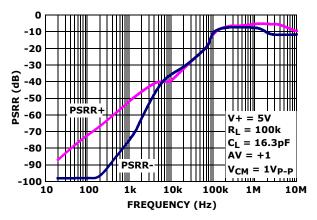


FIGURE 25. PSRR vs FREQUENCY,  $V_S = 5V$ 

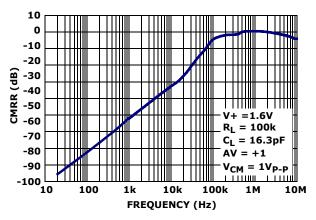


FIGURE 26. CMRR vs FREQUENCY, V<sub>S</sub> = 1.6V

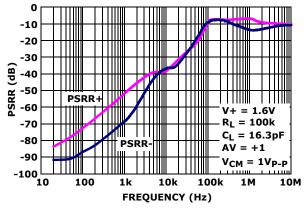


FIGURE 27. PSRR vs FREQUENCY, V<sub>S</sub> = 1.6V

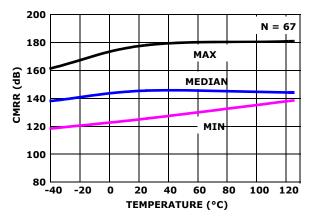


FIGURE 28. CMRR vs TEMPERATURE, VCM = -2.5V TO +2.5V, V+  $= \pm 2.5 V$ 

## **Typical Performance Curves**



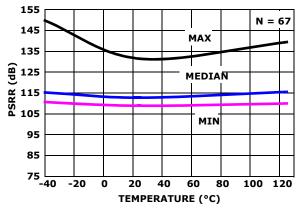


FIGURE 29. PSRR vs TEMPERATURE, V+ = 2V TO 5.5V

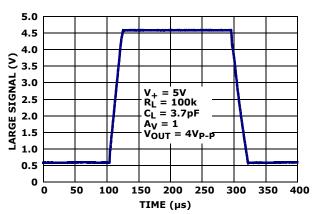


FIGURE 30. LARGE SIGNAL STEP RESPONSE (4V)

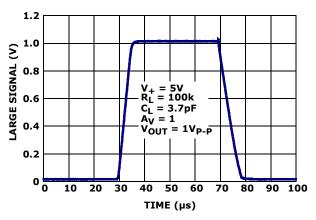


FIGURE 31. LARGE SIGNAL STEP RESPONSE (1V)

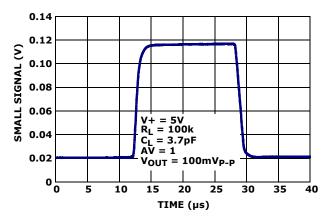


FIGURE 32. SMALL SIGNAL STEP RESPONSE (100mV)

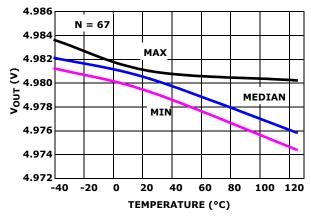


FIGURE 33.  $V_{OUT}$  HIGH vs TEMPERATURE,  $R_L = 10k$ ,  $V_S + -2.5V$ 

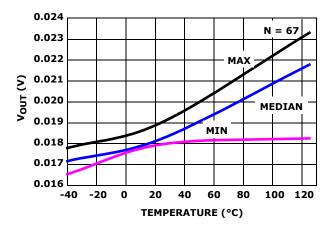


FIGURE 34. V<sub>OUT</sub> LOW vs TEMPERATURE, R<sub>L</sub> = 10k, V<sub>S</sub> +-2.5V

## **Applications Information Functional Description**

The ISL28133 uses a proprietary chopper-stabilized architecture shown in the "Block Diagram" on page 2. The ISL28133 combines a 400kHz main amplifier with a very high open loop gain (174dB) chopper stabilized amplifier to achieve very low offset voltage and drift (2 $\mu$ V, 0.02 $\mu$ V/°C typical) while consuming only 18 $\mu$ A of supply current per channel.

This multi-path amplifier architecture contains a time continuous main amplifier whose input DC offset is corrected by a parallel-connected, high gain chopper stabilized DC correction amplifier operating at 100kHz. From DC to ~5kHz, both amplifiers are active with DC offset correction and most of the low frequency gain is provided by the chopper amplifier. A 5kHz crossover filter cuts off the low frequency amplifier path leaving the main amplifier active out to the 400kHz gain-bandwidth product of the device.

The key benefits of this architecture for precision applications are very high open loop gain, very low DC offset, and low 1/f noise. The noise is virtually flat across the frequency range from a few mHz out to 100kHz, except for the narrow noise peak at the amplifier crossover frequency (5kHz).

#### Rail-to-rail Input and Output (RRIO)

The RRIO CMOS amplifier uses parallel input PMOS and NMOS that enable the inputs to swing 100mV beyond either supply rail. The inverting and non-inverting inputs do not have back-to-back input clamp diodes and are capable of maintaining high input impedance at high differential input voltages. This is effective in eliminating output distortion caused by high slew-rate input signals.

The output stage uses common source connected PMOS and NMOS devices to achieve rail-to-rail output drive capability with 17mA current limit and the capability to swing to within 20mV of either rail while driving a 10k $\Omega$  load.

#### **IN+ and IN- Protection**

All input terminals have internal ESD protection diodes to both positive and negative supply rails, limiting the input voltage to within one diode beyond the supply rails. For applications where either input is expected to exceed the rails by 0.5V, an external series resistor must be used to ensure the input currents never exceed 20mA (see Figure 35).

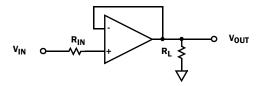


FIGURE 35. INPUT CURRENT LIMITING

#### **Layout Guidelines for High Impedance Inputs**

To achieve the maximum performance of the high input impedance and low offset voltage of the ISL28133 amplifiers, care should be taken in the circuit board layout. The PC board surface must remain clean and free of moisture to avoid leakage currents between adjacent traces. Surface coating of the circuit board will reduce surface moisture and provide a humidity barrier, reducing parasitic resistance on the board.

#### **High Gain, Precision DC-Coupled Amplifier**

The circuit in Figure 36 implements a single-stage, 10kV/V DC-coupled amplifier with an input DC sensitivity of under 100nV that is only possible using a low VOS amplifier with high open loop gain. This circuit is practical down to 1.8V due to it's rail-to-rail input and output capability. Standard high gain DC amplifiers operating from low voltage supplies are not practical at these high gains using typical low offset precision op amps because the input offset voltage and temperature coefficient consume most of the available output voltage swing. For example, a typical precision amplifier in a gain of 10kV/V with a  $\pm 100\mu V$   $V_{OS}$  and a temperature coefficient of  $0.5\mu V/^{\circ}C$  would produce a DC error at the output of >1V with an additional  $5mV^{\circ}C$  of temperature dependent error. At 3V, this DC error consumes > 30% of the total supply voltage, making it impractical to measure sub-microvolt low frequency signals.

The  $\pm 8\mu V$  max  $V_{OS}$  and  $0.075\mu V/^{\circ}C$  of the ISL28133 produces a temperature stable maximum DC output error of only  $\pm 80mV$  with a maximum temperature drift of  $0.75mV/^{\circ}C$ . The additional benefit of a very low 1/f noise corner frequency and some feedback filtering enables DC voltages and voltage fluctuations well below 100nV to be easily detected with a simple single stage amplifier.

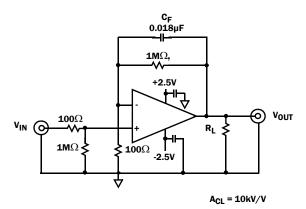


FIGURE 36. HIGH GAIN, PRECISION DC-COUPLED AMPLIFIER

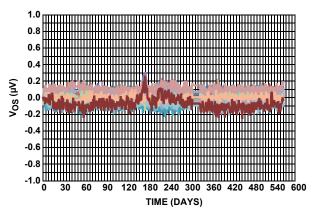


FIGURE 37. LONG TERM DRIFT (VOS vs TIME) FOR 30 UNITS

#### **Long Term Vos Drift**

Figure 37 shows a plot of daily  $V_{OS}$  drift measurements of 30 individual ISL28133 amplifiers over a continuous 572 day period at +25°C. The 30 units were connected in a gain of 10k, mounted on a single PC board and kept at room temp. The 30 amplifier outputs were measured daily by a DVM and scanner under computer control. The daily  $V_{OS}$  measurements were subtracted from the initial  $V_{OS}$  value to calculate the  $V_{OS}$  shift. The test board was powered from a UPS to maintain uninterrupted power to the test units. Three instances of lost measurement data ranging from 2 days to 2 weeks due to power loss to the measurement scanner were detected, and data were interpolated.

The change in amplifier  $V_{OS}$  over the 572 day period for all 30 amplifiers (see Figure 38) was less than  $\pm 100$ nV, and no clear  $V_{OS}$  long term drift trend was evident in the data. The excellent long term drift performance is a result of the chopper amplifier's ability to measure and correct  $V_{OS}$  errors, leaving only the  $V_{OS}$  error contribution due to changes in the long term stability of the external components (see Figure 39).

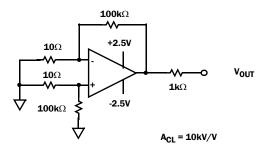


FIGURE 39. LONG TERM DRIFT TEST CIRCUIT

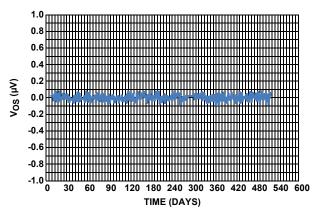


FIGURE 38. LONG TERM DRIFT (VOS VS TIME) FOR A SINGLE UNIT

#### **ISL28133 SPICE Model**

Figure 40 shows the SPICE model schematic and Figure 41 shows the net list for the ISL28133 SPICE model. The model is a simplified version of the actual device and simulates important parameters such as noise, Slew Rate, Gain and Phase. The model uses typical parameters from the ISL28133. The poles and zeros in the model were determined from the actual open and closed-loop gain and phase response. This enables the model to present an accurate AC representation of the actual device. The model is configured for ambient temperature of +25°C.

Figures 42 through 49 show the characterization vs simulation results for the Noise Density, Frequency Response vs Close Loop Gain, Gain vs Frequency vs CL and Large Signal Step Response (4V).

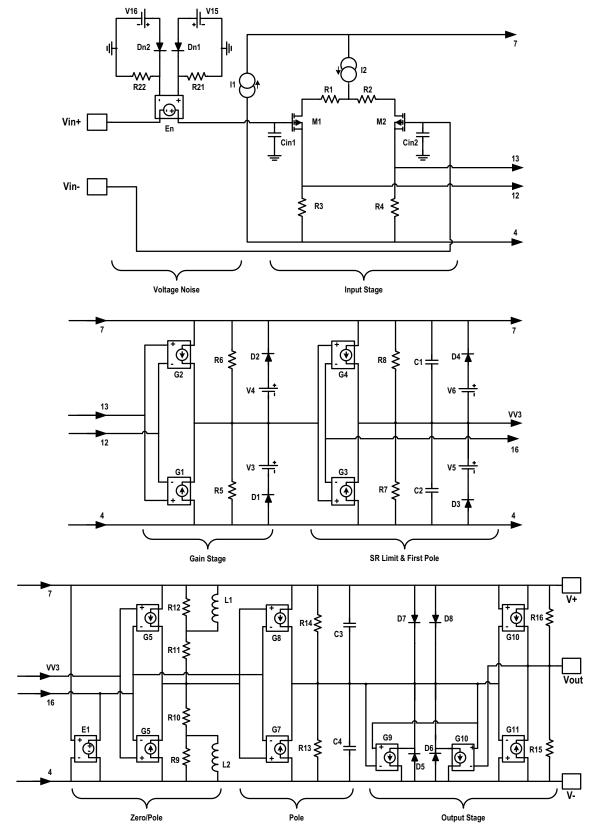


FIGURE 40. SPICE CIRCUIT SCHEMATIC

13

#### ISL28133

```
* ISL28133 Macromodel
                                                           V_V6
                                                                    18 VV3 0.7Vdc
* Revision B, April 2009
* AC characteristics, Voltage Noise
                                                          *Zero/Pole
* Connections:
                     +input
                                                           E E1
                                                                    16 4 7 4 0.5
                          -input
                                                           G G5
                                                                    4 VV4 VV3 16 0.000001
                               +Vsupply
                                                           G G6
                                                                    7 VV4 VV3 16 0.000001
                                    -Vsupply
                                                          L L1
                                                                    20 7 0.3H
                                                           R R12
                                         output
                                                                     20 7 2.5meg
                                                           R R11
                                                                     VV4 20 1meg
.subckt ISL28133
                          2
                                          6
                                                           L_L2
                                                                    4 19 0.3H
                                                           R_R9
                                                                    4 19 2.5meg
*Voltage Noise
                                                           R R10
                                                                     19 VV4 1meg
D DN1
           102 101 DN
                                                           *Pole
D DN2
           104 103 DN
                                                           G G7
                                                                    4 VV5 VV4 16 0.000001
R R21
           0 101 120k
                                                           G G8
                                                                    7 VV5 VV4 16 0.000001
                                                                    VV5 7 0.12p
R R22
          0 103 120k
                                                           C C3
E_EN
          8 3 101 103 1
                                                          C_C4
                                                                    4 VV5 0.12p
V V15
          102 0 0.1Vdc
                                                          R R13
                                                                     4 VV5 1meg
V_V16
          104 0 0.1Vdc
                                                           R_R14
                                                                     VV57 1meg
*Input Stage
                                                           *Output Stage
C_Cin1
           80 0.4p
                                                           G G9
                                                                     21 4 6 VV5 0.0000125
C_Cin2
                                                          G_G10
           20 2.0p
                                                                     22 4 VV5 6 0.0000125
                                                          D_D5
R R1
         9 10 10
                                                                    4 21 DY
R R2
         10 11 10
                                                           D D6
                                                                    4 22 DY
R R3
                                                           D D7
         4 12 100
                                                                    7 21 DX
R R4
         4 13 100
                                                           D D8
                                                                    7 22 DX
M M1
          12899 pmosisil
                                                           R R15
                                                                     46 8k
+ L=50u
                                                           R_R16
                                                                     67 8k
+ W=50u
                                                          G G11
                                                                      6 4 VV5 4 -0.000125
M M2
          13 2 11 11 pmosisil
                                                           G_G12
                                                                      7 6 7 VV5 -0.000125
+ L=50u
+ W=50u
                                                           .model pmosisil pmos (kp=16e-3 vto=10m)
                                                           .model DN D(KF=6.4E-16 AF=1)
1 11
        4 7 DC 92uA
1_12
        7 10 DC 100uA
                                                           .MODEL DX D(IS=1E-18 Rs=1)
                                                           .MODEL DY D(IS=1E-15 BV=50 Rs=1)
*Gain stage
                                                           .ends ISL28133
G G1
         4 VV2 13 12 0.0002
G G2
         7 VV2 13 12 0.0002
R R5
         4 VV2 1.3Meg
R R6
         VV2 7 1.3Meg
D D1
         4 14 DX
D D2
         15 7 DX
V V3
         VV2 14 0.7Vdc
V_V4
         15 VV2 0.7Vdc
*SR limit first pole
G G3
         4 VV3 VV2 16 1
G G4
          7 VV3 VV2 16 1
R R7
         4 VV3 1meg
R R8
         VV3 7 1meg
C C1
         VV3 7 12u
C_C2
         4 VV3 12u
D D3
         4 17 DX
D D4
         18 7 DX
         VV3 17 0.7Vdc
V V5
```

FIGURE 41. SPICE NET LIST

### **Characterization vs Simulation Results**

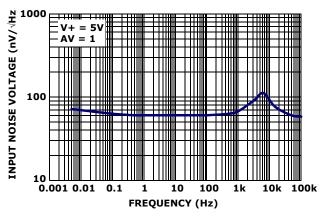


FIGURE 42. CHARACTERIZED INPUT NOISE VOLTAGE DENSITY vs FREQUENCY

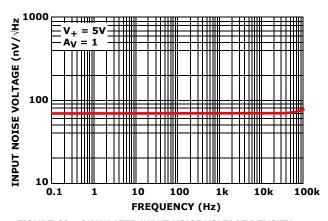


FIGURE 43. SIMULATED INPUT NOISE VOLTAGE DENSITY vs FREQUENCY

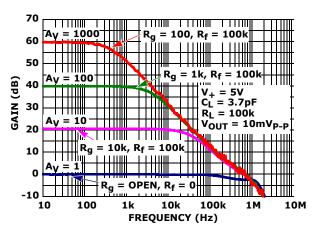


FIGURE 44. CHARACTERIZED FREQUENCY RESPONSE vs CLOSED LOOP GAIN

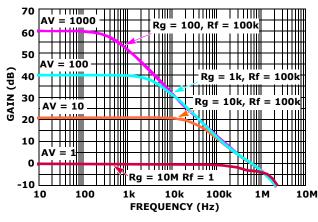


FIGURE 45. SIMULATED FREQUENCY RESPONSE vs CLOSED LOOP GAIN

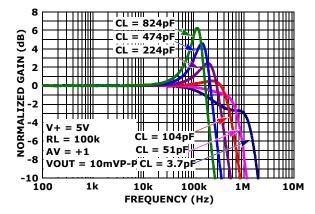


FIGURE 46. CHARACTERIZED GAIN vs FREQUENCY vs CL

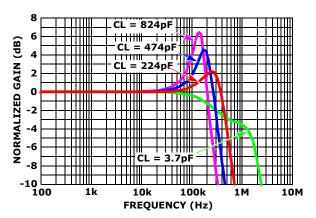


FIGURE 47. SIMULATED GAIN vs FREQUENCY vs CL

## **Characterization vs Simulation Results (Continued)**

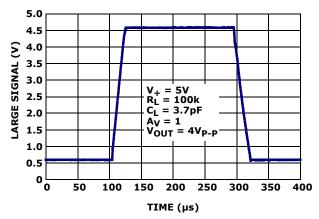


FIGURE 48. CHARACTERIZED LARGE SIGNAL STEP RESPONSE (4V)

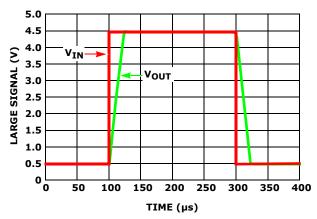


FIGURE 49. SIMULATED LARGE SIGNAL STEP RESPONSE (4V)

## **Revision History**

The revision history provided is for informational purposes only and is believed to be accurate, but not warranted. Please go to web to make sure you have the latest Rev.

DATE	REVISION	CHANGE
2/1/11	FN6560.4	-Converted to Updated Intersil TemplatePage 1 Graphics numbered as Figures 1 and 2Updated Ordering Information on page 2 by adding part ISL28133FHZ-T7AChanged Note on page 5, which read "Parameters with MIN and/or MAX limits are 100% tested at +25°C, unless otherwise specified. Temperature limits established by characterization and are not production tested." to "Compliance to datasheet limits is assured by one or more methods: production test, characterization and/or design." -Added two Long Term Drift Curves (Figures 37 and 38) and section "Long Term VOS Drift" on page 12 -Replaced POD MDP0038 (no dimension changes), now obsolete with P5.064A.
5/3/10	FN6560.3	Title Page 1: Replaced "Zero-Drift" with "Chopper Stabilized" for title and part description On page 3: Pin Configuration: MTDFN -> uTDFN On page 7: Figure 12: Changed 0.1Hz to 0.01Hz in Figure caption On page 11: In "Functional Description"; Paragraph 1, 2nd sentence: Changed text from "open loop gain (200dB)" -to- "open loop gain (174dB)" Changed TYP for "Open Loop Gain" on page 4 from 200dB to 174dB. On page 11: In "High Gain, Precision DC-Coupled Amplifier"; Paragraph 2, 1st sentence: Changed text from "DC output error of only ±80mV with a maximum temperature drift of 0.75mV/°C." to " DC output error of only ±80mV with a maximum temperature drift of 0.75mV/°C."
2/24/10	=	Removed "Coming Soon" from ISL28133EVAL1Z in the ordering information table on pg 2.
09/24/09	FN6560.2	Converted to new Intersil template. Removed ISL28233 and ISL28433 from data sheet, added Applications, Related Literature, Typical Application Circuit, Performance Curve, updated ordering information by removing "coming soon" on SC70 and uTDFN packages and adding Eval board listed as "coming soon". Added Block Diagram, Changed in Abs Max Rating Voltage from "5.75V" to "6.5V". Removed Tjc from Thermal Information until provided by packaging scheduled for 9-11-09. Changed Low Offset "drift" to Low Offset "TC", added Max Junction Temp 140C, added SPICE model and simulation results, removed supply current graph at +-3V, re-ordered typical performance curves, removed guard ring information from application section. Added Revision History and Products Information
05/29/09	FN6560.1	Page 4: Removed the RL = 100 Curve from Figures 3, 4 and 5. Page 1: Under Features, removed the word "Output" from "Low Output Noise"
03/25/09	FN6560.0	Initial Release to WEB

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\*For a complete listing of Applications, Related Documentation and Related Parts, please see the respective device information page on intersil.com: <a href="ISL28133">ISL28133</a></a>

To report errors or suggestions for this data sheet, please go to www.intersil.com/askourstaff

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## Small Outline Transistor Plastic Packages (SC70-5)

## VIEW C Ε ፍ ፍ 3 b 0.20 (0.008) M ፍ **SEATING PLANE** -C-0.10 (0.004) C WITH **PLATING 1** c1 **BASE METAL** 4X θ1 GAUGE PLANE SEATING **PLANE** С 4X θ1 ~ VIEW C 2.1mm → 0.65mm

P5.049 **5 LEAD SMALL OUTLINE TRANSISTOR PLASTIC PACKAGE** 

	INCHES		MILLIM	ETERS	
SYMBOL	MIN	MAX	MIN	MAX	NOTES
Α	0.031	0.043	0.80	1.10	-
A1	0.000	0.004	0.00	0.10	-
A2	0.031	0.039	0.80	1.00	-
b	0.006	0.012	0.15	0.30	-
b1	0.006	0.010	0.15	0.25	
С	0.003	0.009	0.08	0.22	6
c1	0.003	0.009	0.08	0.20	6
D	0.073	0.085	1.85	2.15	3
E	0.071	0.094	1.80	2.40	-
E1	0.045	0.053	1.15	1.35	3
е	0.025	6 Ref	0.65	Ref	-
e1	0.0512 Ref		1.30	Ref	-
L	0.010	0.018	0.26	0.46	4
L1	0.017	Ref.	0.420	Ref.	-
L2	0.006	BSC	0.15 BSC		
α	0°	8 <sup>0</sup>	0°	8 <sup>0</sup>	-
N	5		Į.	5	5
R	0.004	-	0.10	-	
R1	0.004	0.010	0.15	0.25	0.7/07

Rev. 3 7/07

#### NOTES:

- 1. Dimensioning and tolerances per ASME Y14.5M-1994.
- 2. Package conforms to EIAJ SC70 and JEDEC MO-203AA.
- 3. Dimensions D and E1 are exclusive of mold flash, protrusions, or gate burrs.
- 4. Footlength L measured at reference to gauge plane.
- 5. "N" is the number of terminal positions.
- 6. These Dimensions apply to the flat section of the lead between 0.08mm and 0.15mm from the lead tip.
- 7. Controlling dimension: MILLIMETER. Converted inch dimensions are for reference only.

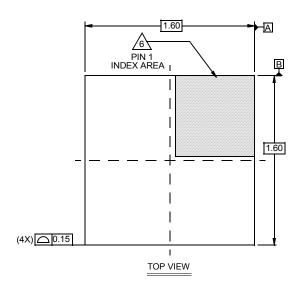
TYPICAL RECOMMENDED LAND PATTERN

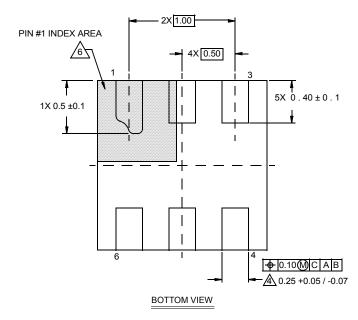
### **Package Outline Drawing**

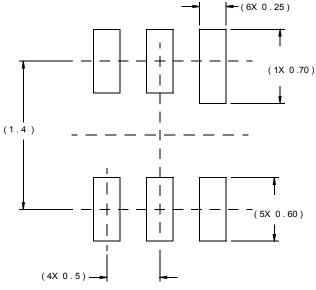
#### L6.1.6x1.6

#### 6 LEAD ULTRA THIN DUAL FLAT NO-LEAD COL PLASTIC PACKAGE (UTDFN COL)

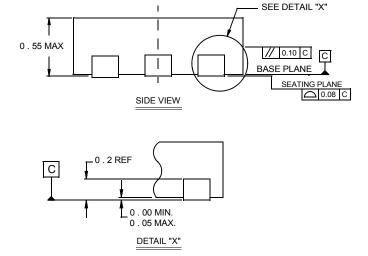
Rev 1, 11/07







TYPICAL RECOMMENDED LAND PATTERN



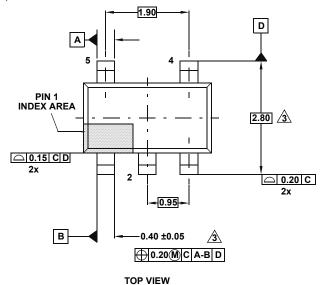
#### NOTES:

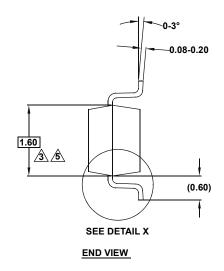
- Dimensions are in millimeters.
   Dimensions in ( ) for Reference Only.
- 2. Dimensioning and tolerancing conform to AMSE Y14.5m-1994.
- 3. Unless otherwise specified, tolerance : Decimal  $\pm 0.05$
- 4. Dimension b applies to the metallized terminal and is measured between 0.15mm and 0.30mm from the terminal tip.
- 5. Tiebar shown (if present) is a non-functional feature.
- The configuration of the pin #1 identifier is optional, but must be located within the zone indicated. The pin #1 identifier may be either a mold or mark feature.

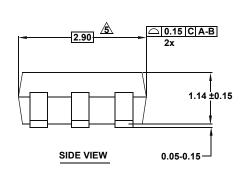
## **Package Outline Drawing**

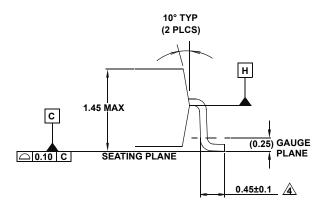
#### P5.064A

5 LEAD SMALL OUTLINE TRANSISTOR PLASTIC PACKAGE Rev 0, 2/10









(2.40)

(2.40)

(2.40)

(2.40)

(3.40)

(4.90)

TYPICAL RECOMMENDED LAND PATTERN

NOTES:

Dimensions are in millimeters.
 Dimensions in ( ) for Reference Only.

DETAIL "X"

- 2. Dimensioning and tolerancing conform to ASME Y14.5M-1994.
- 3. Dimension is exclusive of mold flash, protrusions or gate burrs.
- 4. Foot length is measured at reference to guage plane.
- 5. This dimension is measured at Datum "H".
- 6. Package conforms to JEDEC MO-178AA.